

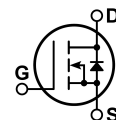
## N-Channel FREDFET

Power MOS 8™ is a high speed, high voltage N-channel switch-mode power MOSFET. A proprietary planar stripe design yields excellent reliability and manufacturability. Low switching loss is achieved with low input capacitance and ultra low  $C_{rss}$  "Miller" capacitance. The intrinsic gate resistance and capacitance of the poly-silicon gate structure help control slew rates during switching, resulting in low EMI and reliable paralleling, even when switching at very high frequency. Reliability in flyback, boost, forward, and other circuits is enhanced by the high avalanche energy capability.



ISOTOP™  
**APT100F50J**

Single die FREDFET



### FEATURES

- Fast switching with low EMI
- Low  $t_{rr}$  for high reliability
- Ultra low  $C_{rss}$  for improved noise immunity
- Low gate charge
- Avalanche energy rated
- RoHS compliant

### TYPICAL APPLICATIONS

- ZVS phase shifted and other full bridge
- Half bridge
- PFC and other boost converter
- Buck converter
- Single and two switch forward
- Flyback

### Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
$I_D$	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	103	A
	Continuous Drain Current @ $T_C = 100^\circ\text{C}$	65	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	490	
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulse Avalanche Energy <sup>②</sup>	3350	mJ
$I_{AR}$	Avalanche Current, Repetitive or Non-Repetitive	75	A

### Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$			960	W
$R_{\theta JC}$	Junction to Case Thermal Resistance			0.13	$^\circ\text{C/W}$
$R_{\theta CS}$	Case to Sink Thermal Resistance, Flat, Greased Surface		0.15		
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55		150	$^\circ\text{C}$
$V_{Isolation}$	RMS Voltage (50-60Hz Sinusoidal Waveform from Terminals to Mounting Base for 1 Min.)	2500			V
$W_T$	Package Weight		1.03		oz
			29.2		g
Torque	Terminals and Mounting Screws.			10	in·lbf
				1.1	N·m

**Static Characteristics**
**T<sub>J</sub> = 25°C unless otherwise specified**
**APT100F50J**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{BR(DSS)}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	500			V
$\Delta V_{BR(DSS)}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to 25°C, $I_D = 250\mu A$		0.60		V/°C
$R_{DS(on)}$	Drain-Source On Resistance <sup>③</sup>	$V_{GS} = 10V, I_D = 75A$		.28	0.036	Ω
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5mA$	2.5	4	5	V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold Voltage Temperature Coefficient			-10		mV/°C
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 500V$ $V_{GS} = 0V$			250	μA
		$T_J = 25^\circ C$ $T_J = 125^\circ C$			1000	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS} = \pm 30V$			±100	nA

**Dynamic Characteristics**
**T<sub>J</sub> = 25°C unless otherwise specified**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$g_{fs}$	Forward Transconductance	$V_{DS} = 50V, I_D = 75A$		115		S
$C_{iss}$	Input Capacitance	$V_{GS} = 0V, V_{DS} = 25V$ $f = 1MHz$		24600		pF
$C_{rss}$	Reverse Transfer Capacitance			330		
$C_{oss}$	Output Capacitance			2645		
$C_{o(cr)}^{④}$	Effective Output Capacitance, Charge Related	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 333V$		1535		
$C_{o(er)}^{⑤}$	Effective Output Capacitance, Energy Related			775		
$Q_g$	Total Gate Charge	$V_{GS} = 0 \text{ to } 10V, I_D = 75A,$ $V_{DS} = 250V$		620		nC
$Q_{gs}$	Gate-Source Charge			140		
$Q_{gd}$	Gate-Drain Charge			280		
$t_{d(on)}$	Turn-On Delay Time	<b>Resistive Switching</b> $V_{DD} = 333V, I_D = 75A$ $R_G = 2.2\Omega^{⑥}, V_{GG} = 15V$		105		ns
$t_r$	Current Rise Time			125		
$t_{d(off)}$	Turn-Off Delay Time			280		
$t_f$	Current Fall Time			90		

**Source-Drain Diode Characteristics**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$I_S$	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode (body diode)			103	A
$I_{SM}$	Pulsed Source Current (Body Diode) <sup>①</sup>				490	
$V_{SD}$	Diode Forward Voltage	$I_{SD} = 75A, T_J = 25^\circ C, V_{GS} = 0V$			1.2	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 75A^{③}$ $di_{SD}/dt = 100A/\mu s$ $V_{DD} = 100V$	$T_J = 25^\circ C$	340	390	ns
			$T_J = 125^\circ C$	603	720	
$Q_{rr}$	Reverse Recovery Charge		$T_J = 25^\circ C$	2.74		μC
			$T_J = 125^\circ C$	7.29		
$I_{rrm}$	Reverse Recovery Current		$T_J = 25^\circ C$	15.2		A
			$T_J = 125^\circ C$	23.4		
dv/dt	Peak Recovery dv/dt	$I_{SD} \leq 75A, di/dt \leq 1000A/\mu s, V_{DD} = 333V,$ $T_J = 125^\circ C$			20	V/ns

① Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

② Starting at  $T_J = 25^\circ C, L = 1.19mH, R_G = 25\Omega, I_{AS} = 75A$ .

③ Pulse test: Pulse Width < 380μs, duty cycle < 2%.

④  $C_{o(cr)}$  is defined as a fixed capacitance with the same stored charge as  $C_{OSS}$  with  $V_{DS} = 67\%$  of  $V_{(BR)DSS}$ .

⑤  $C_{o(er)}$  is defined as a fixed capacitance with the same stored energy as  $C_{OSS}$  with  $V_{DS} = 67\%$  of  $V_{(BR)DSS}$ . To calculate  $C_{o(er)}$  for any value of  $V_{DS}$  less than  $V_{(BR)DSS}$ , use this equation:  $C_{o(er)} = -5.71E-7/V_{DS}^2 + 1.33E-7/V_{DS} + 3.80E-10$ .

⑥  $R_G$  is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

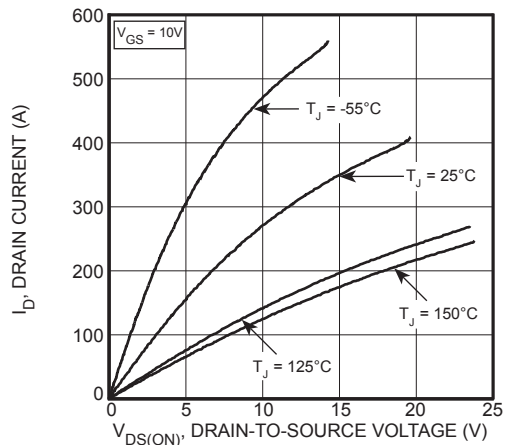


Figure 1, Output Characteristics

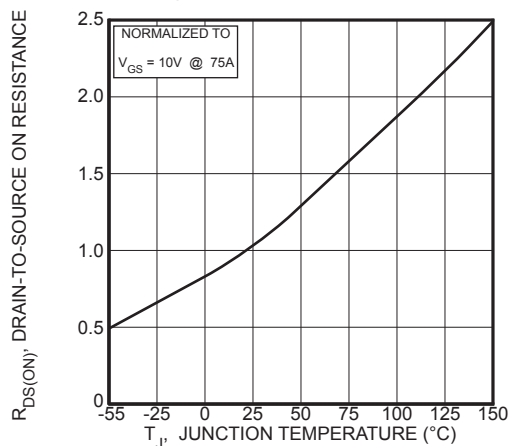
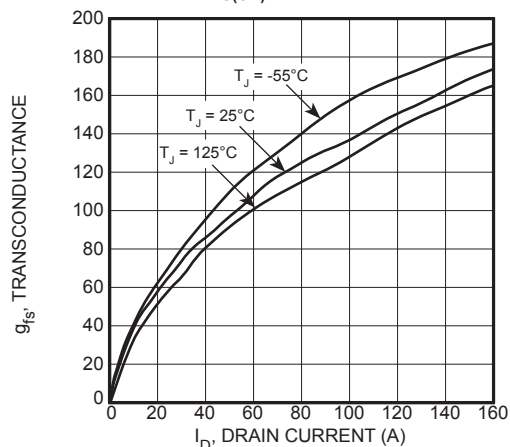
Figure 3,  $R_{DS(ON)}$  vs Junction Temperature

Figure 5, Gain vs Drain Current

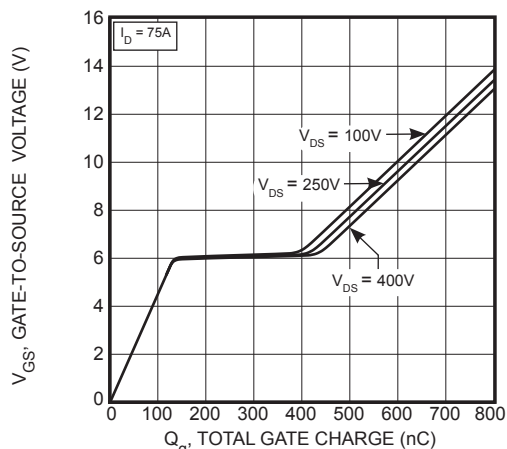


Figure 7, Gate Charge vs Gate-to-Source Voltage

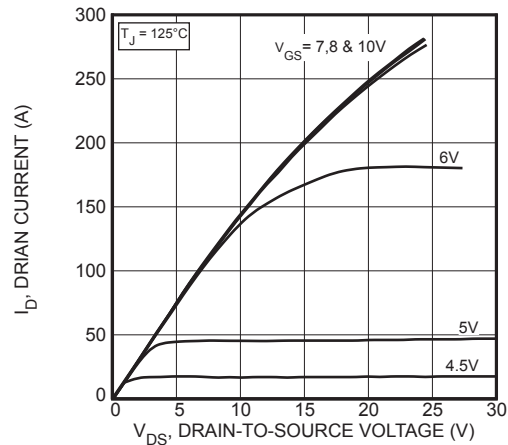


Figure 2, Output Characteristics

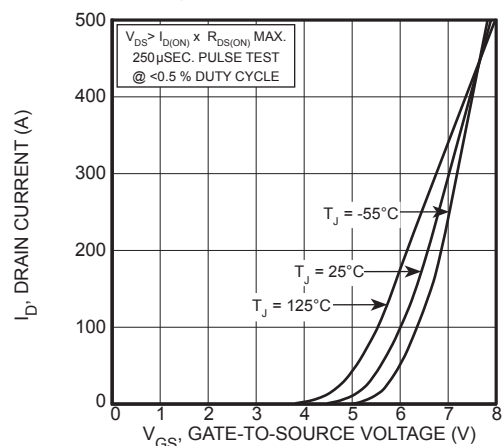


Figure 4, Transfer Characteristics

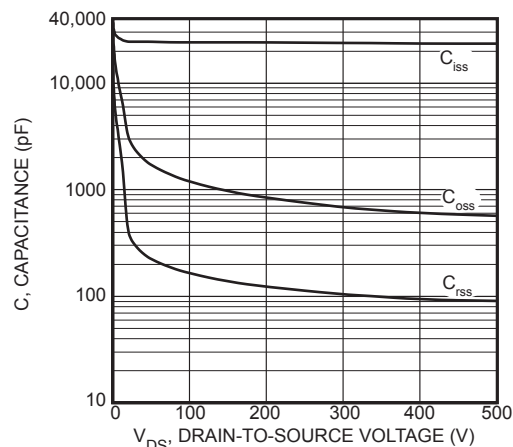


Figure 6, Capacitance vs Drain-to-Source Voltage

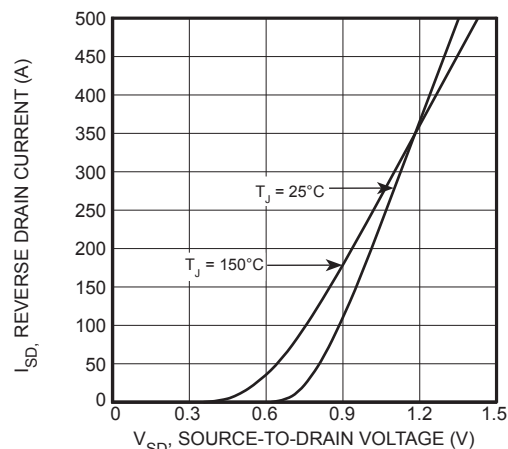


Figure 8, Reverse Drain Current vs Source-to-Drain Voltage

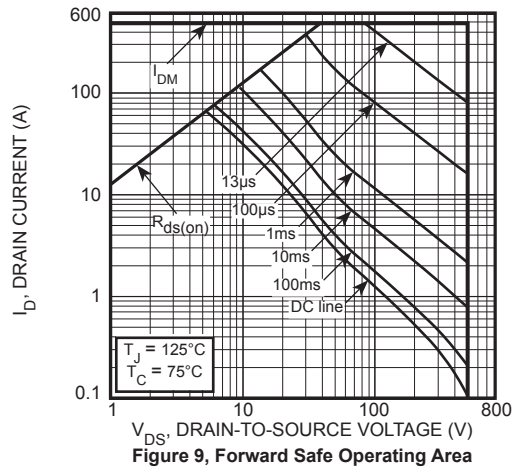


Figure 9, Forward Safe Operating Area

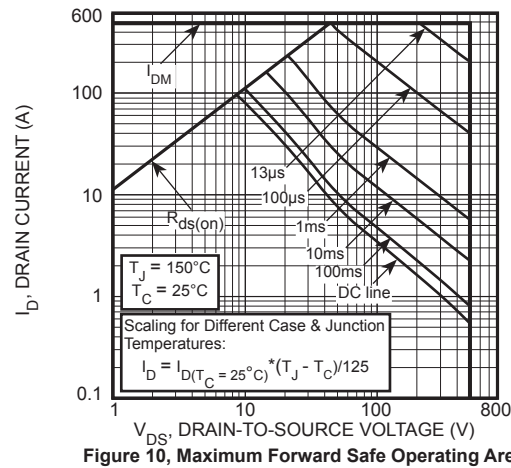


Figure 10, Maximum Forward Safe Operating Area

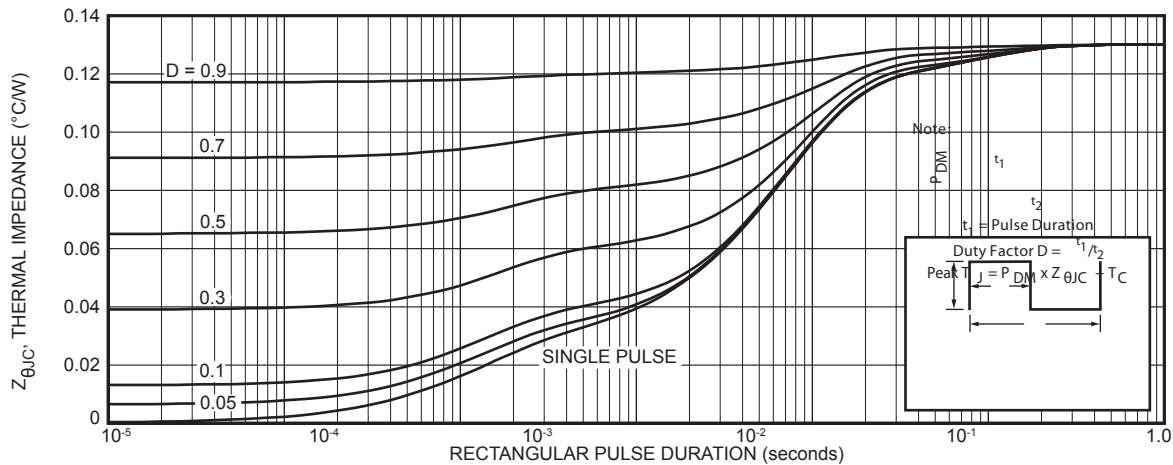
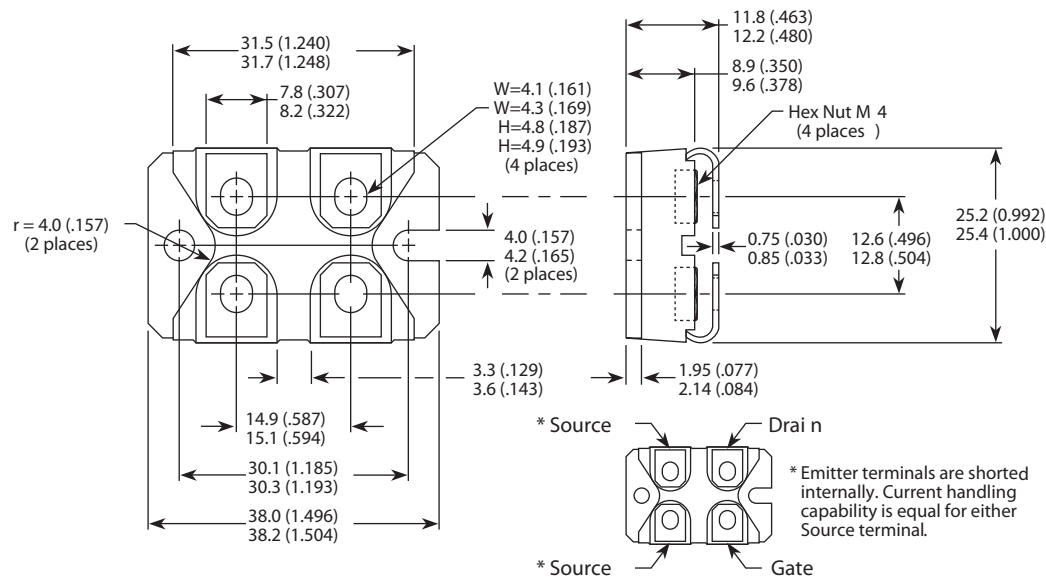


Figure 11. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)